



TO-92L Plastic-Encapsulate Transistors

KSA928A TRANSISTOR (PNP)

FEATURE

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

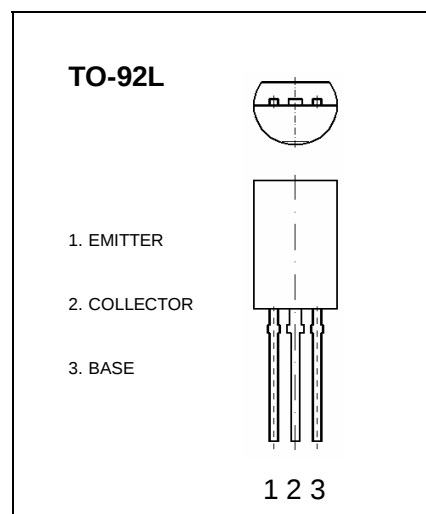
I_{CM} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$		-2	V
Base-emitter voltage	V_{BE}	$I_C = -500mA, V_{CE} = -2V$		-1	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -500mA$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320